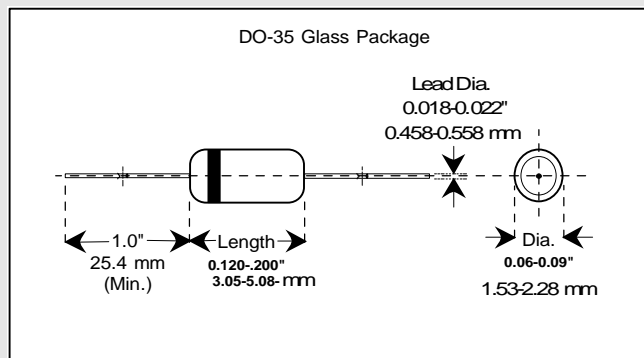


Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	200	mAmps	
Peak Surge Current (t _{peak} = 1 sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation T _L =50 °C, L = 3/8" from body	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +200	° C	
Storage Temperature Range	T _{St}	-65 to +200	° C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

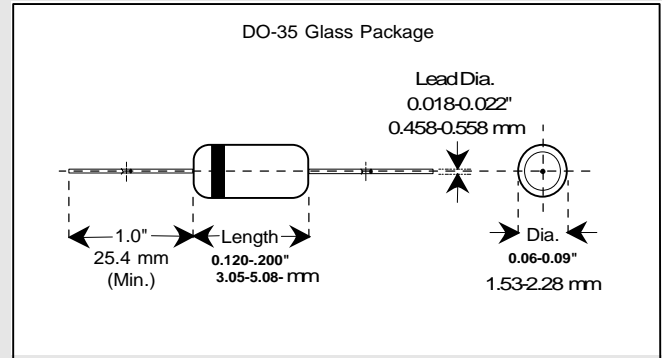
Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

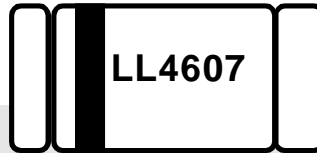
- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I_{avg}	200	mAmps	
Continuous Forward Current	I_{Fdc}	500	mAmps	
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)	I_{peak}	1.0	Amp	
BKC Power Dissipation $T_L = 50^\circ\text{C}$, $L = 3/8"$ from body	P_{tot}	500	mWatts	
Operating Temperature Range	T_{Op}	-65 to +150	$^\circ\text{C}$	
Storage Temperature Range	T_{St}	-65 to +150	$^\circ\text{C}$	
Electrical Characteristics @ 25 $^\circ\text{C}$ *	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$	V_F	***	1.10	Volts
Breakdown Voltage @ $I_R = 25 \mu\text{A}$	PIV	85		Volts
Reverse Leakage Current @ $V_R = 50 \text{ V}$	I_R		100	μA
Reverse Recovery time (note 1)	t_{rr}		10	nSecs

Note 1: Per Method 4031-A with $I_F = 10 \text{ mA}$, $V_r = 6 \text{ V}$, $R_L = 100 \text{ Ohms}$. * UNLESS OTHERWISE SPECIFIED

Silicon Switching Diode



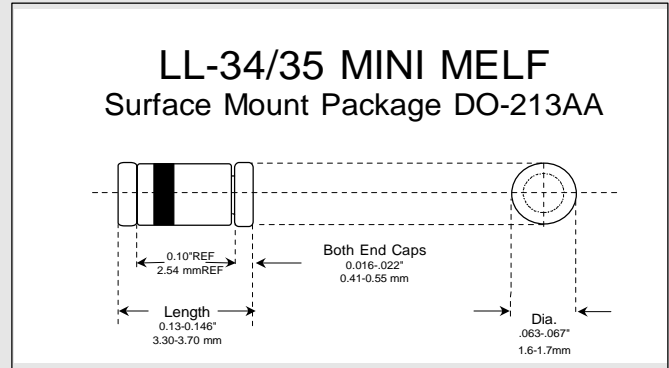
L-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

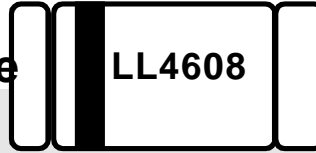
- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	200	mAmps	
Peak Surge Current (t _{peak} = 1 sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +200	°C	
Storage Temperature Range	T _{St}	-65 to +200	°C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_R = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

Silicon Switching Diode



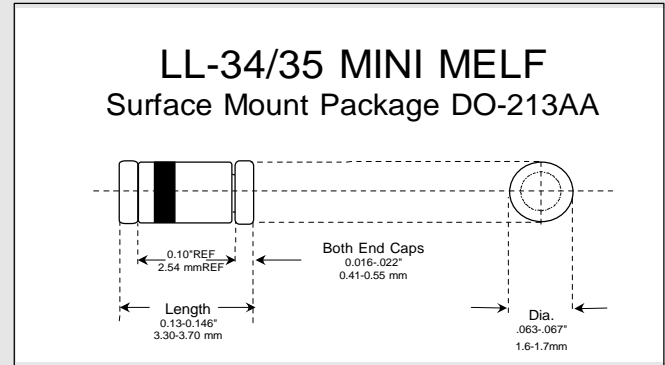
LL-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	500	mAmps	
Peak Surge Current (t _{peak} = 1 sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation T _L =50 °C, L = 3/8" from body	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +150	°C	
Storage Temperature Range	T _{St}	-65 to +150	°C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED



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